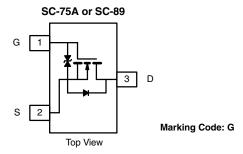




N-Channel 1.5 V (G-S) MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|---------------------------------|---------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (mA) | | | |
| 20 | 5 at V _{GS} = 4.5 V | 200 | | | |
| | 7 at V _{GS} = 2.5 V | 175 | | | |
| | 9 at V _{GS} = 1.8 V | 150 | | | |
| | 10 at V _{GS} = 1.5 V | 50 | | | |



Ordering Information:

Si1032R-T1-GE3 (SC-75A, Lead (Pb)-free and Halogen-free) Si1032X-T1-GE3 (SC-89, Lead (Pb)-free -free Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low-Side Switching
- Low On-Resistance: 5 Ω
- Low Threshold: 0.9 V (typ.)
- Fast Switching Speed: 35 ns
- TrenchFET[®] Power MOSFETs: 1.5 V Rated
- 2000 V ESD Protection
- · Compliant to RoHS Directive 2002/95/EC

BENEFITS

- · Ease in Driving Switches
- · Low Offset (Error) Voltage
- · Low-Voltage Operation
- High-Speed Circuits
- · Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Load/Power Switching Cell Phones, Pagers

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | | | | |
|---|------------------------|-----------------------------------|--------------|-----|--------------|------|----|
| | | | Si1032R | | Si1032X | | |
| Parameter | Symbol | 5 s | Steady State | 5 s | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | 20 | | | | V | |
| Gate-Source Voltage | | V_{GS} | ± 6 | | | | |
| 0 D . 0 (T 150.00) | T _A = 25 °C | - I _D | 200 | 140 | 210 | 200 | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 85 °C | | 110 | 100 | 150 | 140 | |
| Pulsed Drain Current ^a | | I _{DM} | 500 | | 600 | | mA |
| Continuous Source Current (Diode Conduction) ^a | | I _S | 250 | 200 | 300 | 240 | |
| | T _A = 25 °C | | 280 | 250 | 340 | 300 | mW |
| Maximum Power Dissipation ^a for SC-75 | T _A = 85 °C | | 145 | 130 | 170 | 150 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | | • | °C |
| Gate-Source ESD Rating (HBM, Method 3015) | | ESD | 2000 | | | | V |

Notes:

a. Surface mounted on FR4 board.

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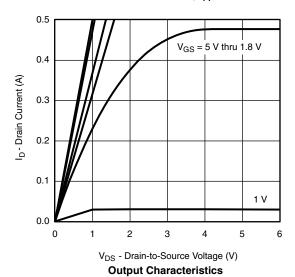
| SPECIFICATIONS (T _A = 25 °C, unless otherwise noted) | | | | | | | | | |
|--|---------------------|--|------|-------|-------|------|--|--|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | | | |
| Static | | | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 0.40 | 0.7 | 1.2 | V | | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 2.8 \text{ V}$ | | ± 0.5 | ± 1.0 | | | | |
| | | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$ ± 1.0 | | | | | | | |
| Zarra Cata Valtaria Dunin Comment | | V _{DS} = 20 V, V _{GS} = 0 V | | | 1 | - μΑ | | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | 10 | = | | | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} = 5 V, V _{GS} = 4.5 V | 250 | | | mA | | | |
| | R _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$ | | | 5 | | | | |
| | | $V_{GS} = 2.5 \text{ V}, I_D = 175 \text{ mA}$ | | | 7 | Ω | | | |
| Drain-Source On-State Resistance ^a | | $V_{GS} = 1.8 \text{ V}, I_D = 150 \text{ mA}$ | | | 9 | | | | |
| | | $V_{GS} = 1.5 \text{ V}, I_D = 40 \text{ mA}$ | | | 10 | | | | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 10 V, I _D = 200 mA | | 0.5 | | S | | | |
| Diode Forward Voltage ^a | V_{SD} | I _S = 150 mA, V _{GS} = 0 V | | | 1.2 | V | | | |
| Dynamic ^b | | | | | | | | | |
| Total Gate Charge | Q_g | | | 750 | | | | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 250 \text{ mA}$ | | 75 | | рC | | | |
| Gate-Drain Charge | Q_{gd} | | | 225 | | | | | |
| Turn-On Delay Time | t _{d(on)} | | | | 50 | | | | |
| Rise Time | t _r | V_{DD} = 10 V, R_L = 47 Ω | | | 25 | ns | | | |
| Turn-Off Delay Time | t _{d(off)} | $\rm I_D\cong 200$ mA, $\rm V_{GEN}$ = 4.5 V, $\rm R_g$ = 10 $\rm \Omega$ | | | 50 | | | | |
| Fall Time | t _f | | | | 25 | | | | |

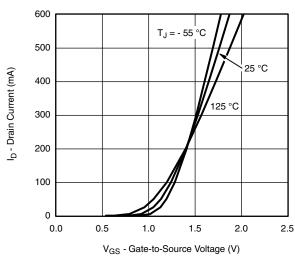
Notes:

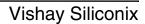
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

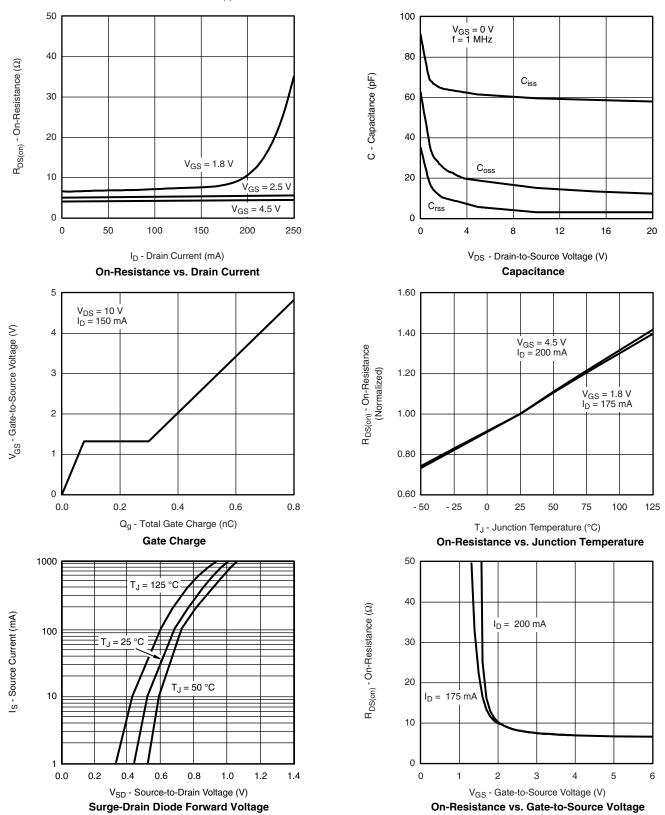








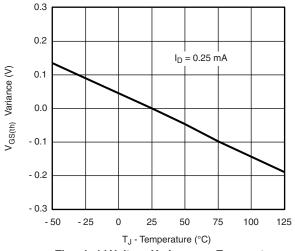
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

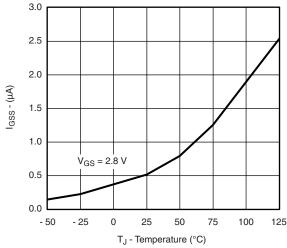


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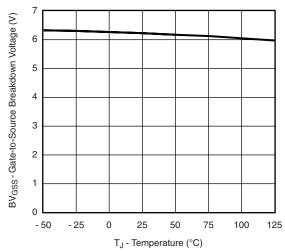
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



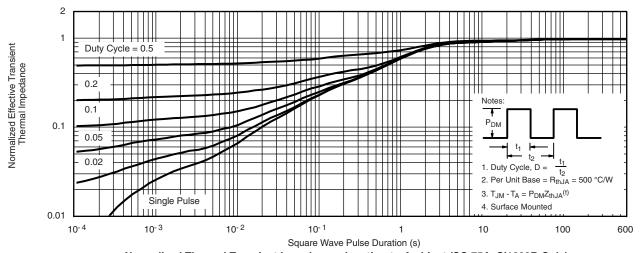


Threshold Voltage Variance vs. Temperature





BV_{GSS} vs. Temperature

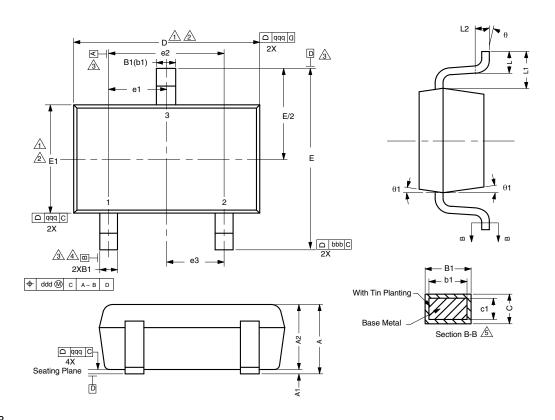


Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A, Si1032R Only)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71172.



SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

1 Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.

2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interelead flash, but including any mismatch between the top and bottom of the plastic body.

2 Datums A, B and D to be determined 0.10 mm from the lead tip.

4. Terminal positions are shown for reference only.

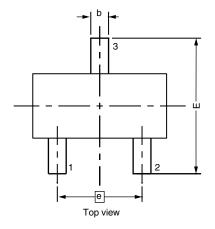
These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

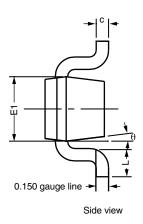
| 0.10 |
|------|
| |
| 0.10 |
| 0.10 |
| 0.10 |
| |

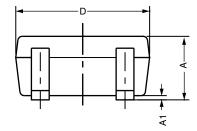
| DIM. | N | | | |
|----------------|-----------|----------|------|------|
| DIIVI. | MIN. | NOM. | MAX. | NOTE |
| Α | - | - | 0.80 | |
| A ₁ | 0.00 | - | 0.10 | |
| A ₂ | 0.65 | 0.70 | 0.80 | |
| B ₁ | 0.19 | - | 0.24 | 5 |
| b ₁ | 0.17 | - | 0.21 | |
| С | 0.13 | - | 0.15 | 5 |
| C ₁ | 0.10 | - | 0.12 | 5 |
| D | 1.48 | 1.575 | 1.68 | 1, 2 |
| E | 1.50 | 1.60 | 1.70 | |
| E ₁ | 0.66 | 0.76 | 0.86 | 1, 2 |
| e ₁ | | 0.50 BSC | | |
| e ₂ | 1.00 BSC | | | |
| e ₃ | 0.50 BSC | | | |
| L | 0.15 | 0.205 | 0.30 | |
| L ₁ | 0.40 ref. | | | |
| L ₂ | 0.15 BSC | | | |
| θ | 0° | - | 8° | |
| θ ₁ | 4° | - | 10° | |

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For Samsung only







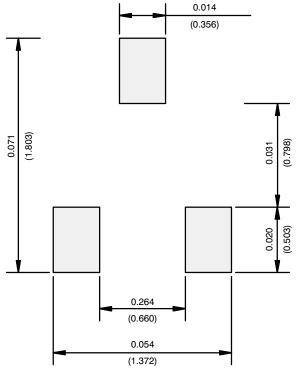
Notes

- (1) Millimeters will govern.
- (2) Dimension exclusive of mold gate burrs.
- (3) Dimension exclusive of mold flash and cutting burrs.

| DIM. | | MILLIMETERS | | INCHES | | | |
|------|------|-------------|------|--------|-------|-------|--|
| DIN. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| Α | 0.60 | 0.70 | 0.80 | 0.024 | 0.028 | 0.031 | |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 | |
| b | 0.18 | 0.22 | 0.32 | 0.007 | 0.009 | 0.013 | |
| С | 0.11 | 0.13 | 0.21 | 0.004 | 0.005 | 0.008 | |
| D | 1.48 | 1.58 | 1.68 | 0.058 | 0.062 | 0.066 | |
| E | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 | |
| E1 | 0.66 | 0.76 | 0.86 | 0.026 | 0.030 | 0.034 | |
| е | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 | |
| L | 0.22 | 0.32 | 0.42 | 0.009 | 0.013 | 0.017 | |
| θ | 4° | 7° | 10° | 4° | 7° | 10° | |



RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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